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LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 30 A
V_{RRM}	30 V
$T_j(\text{max})$	150 °C
$V_F(\text{max})$	0.38 V

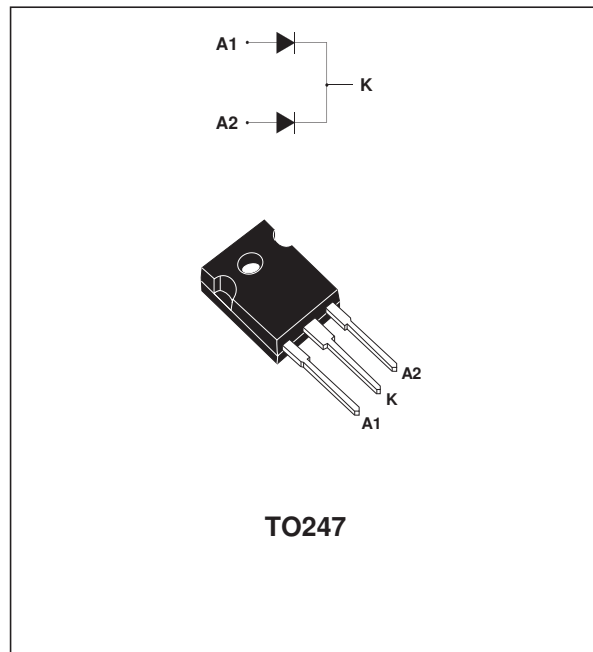
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in TO247, this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



TO247

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		50	A
$I_{F(AV)}$	Average forward current	$T_c = 130^\circ\text{C}$ $\delta = 0.5$	Per diode: 30 Per device: 60	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	600	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2 \mu\text{s}$ $F = 1 \text{ kHz}$ square	2	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$	11000	W
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise reverse voltage		10000	V/ μs

* $\therefore \frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS60L30CW

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.8	$^{\circ}\text{C}/\text{W}$
		Total	0.45	
$R_{th(c)}$		Coupling	0.1	$^{\circ}\text{C}/\text{W}$

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			4	mA
		$T_j = 125^{\circ}\text{C}$			250	500	
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{ A}$			0.46	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{ A}$		0.33	0.38	
		$T_j = 25^{\circ}\text{C}$	$I_F = 60\text{ A}$			0.55	
		$T_j = 125^{\circ}\text{C}$	$I_F = 60\text{ A}$		0.45	0.5	

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.26 \times I_{F(AV)} + 0.004 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

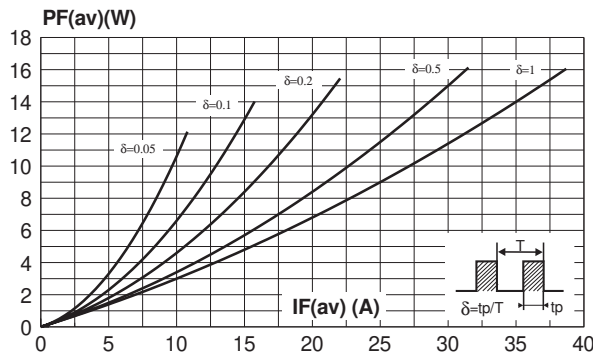


Fig. 3: Normalized avalanche power derating versus pulse duration.

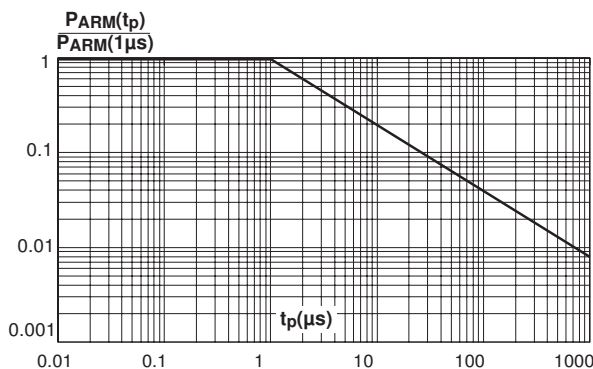


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$) (per diode).

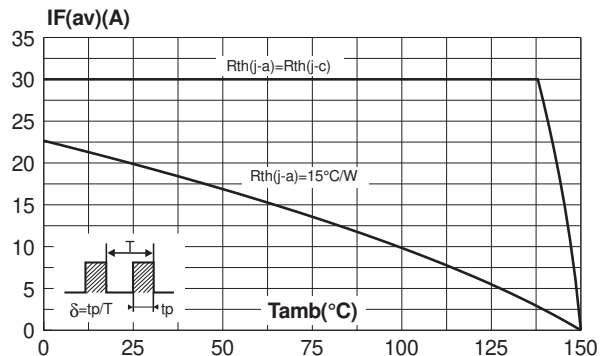


Fig. 4: Normalized avalanche power derating versus junction temperature.

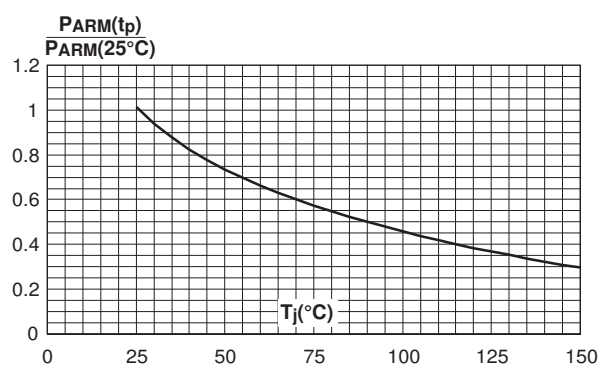


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

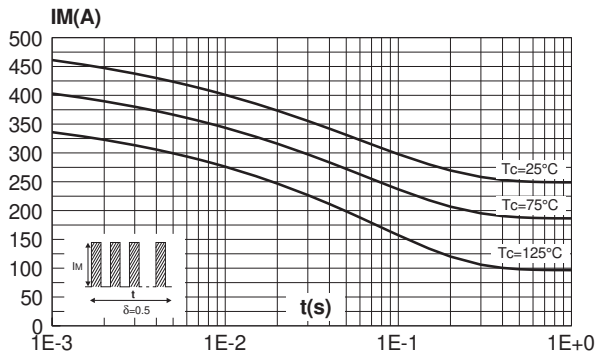


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

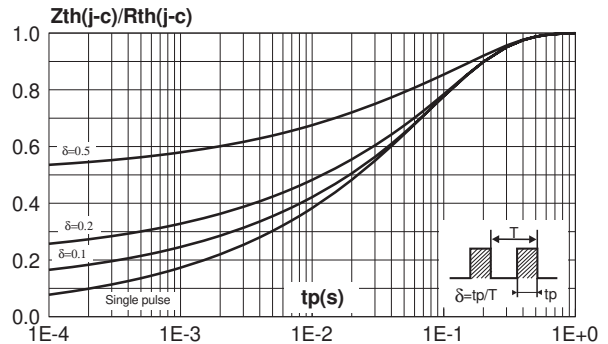


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

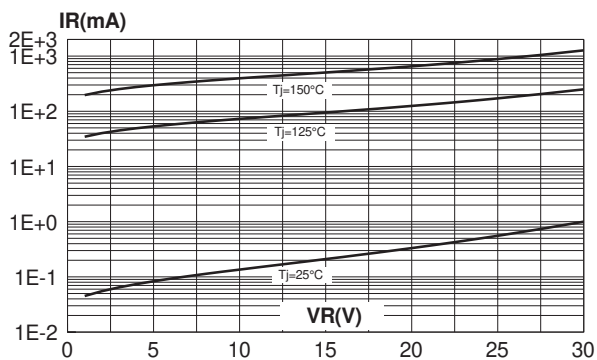


Fig. 8: Junction capacitance versus reverse voltage applied (typical values) (per diode).

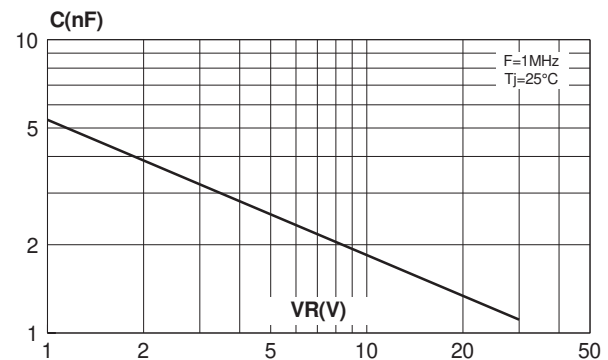
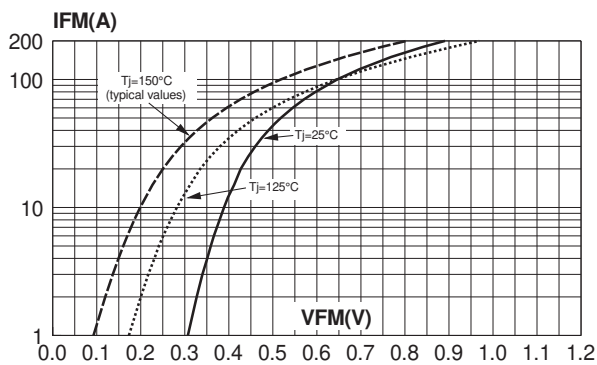
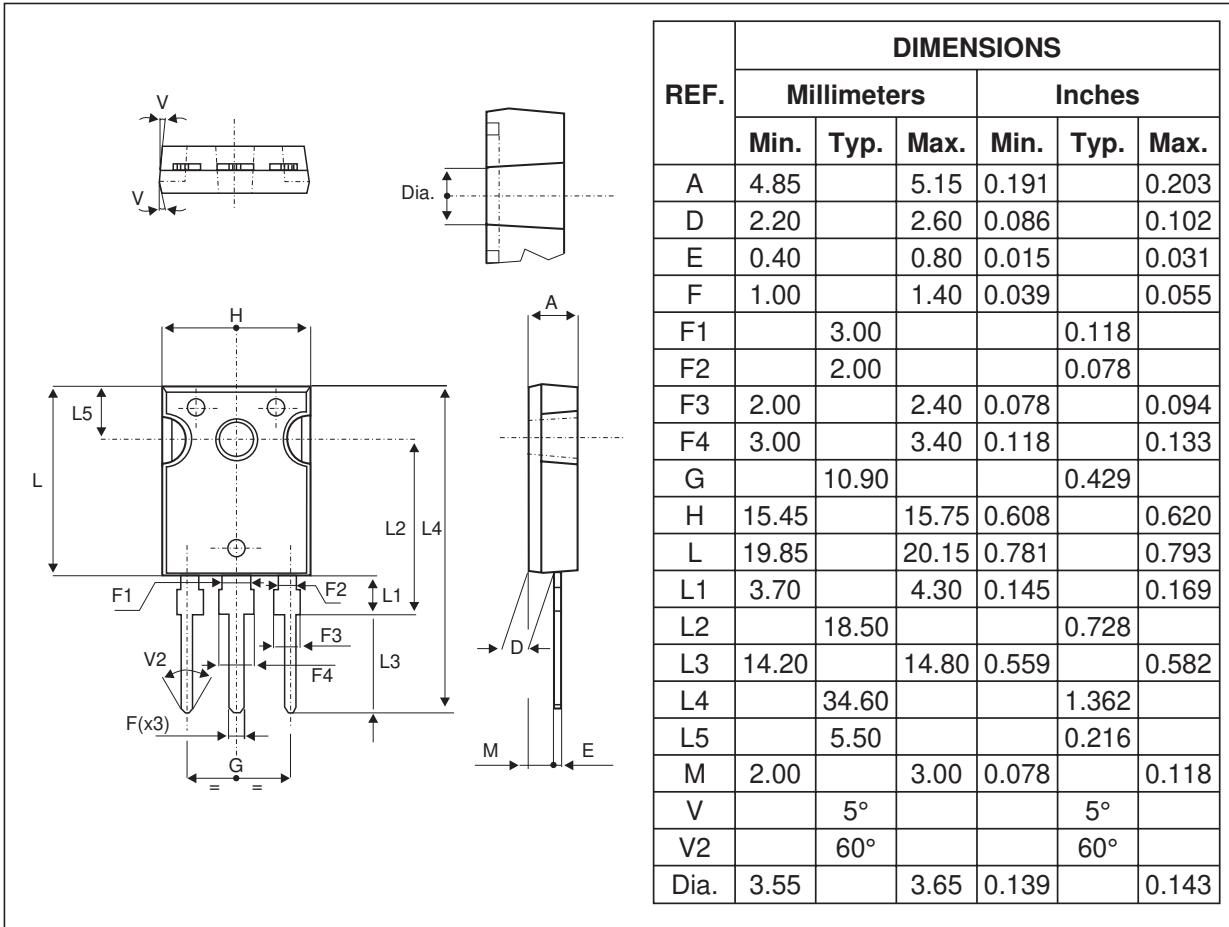


Fig. 9: Forward voltage drop versus forward current (maximum values - per diode).



STPS60L30CW
PACKAGE MECHANICAL DATA
 TO247



- Cooling method: C
- Recommended torque value: 0.8 m.N
- Maximum torque value: 1 m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS60L30CW	STPS60L30CW	TO247	4.36g	30	Tube

- Epoxy meets UL94,V0

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